Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	765	(438/787).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:15
S2	553	(438/788).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S3	338	(438/789).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S4	376	(438/790).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S5	425	(438/791).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
S6	265	(438/792).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
S7	50	(438/793).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 09:45
S8	53	(438/794).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 09:46
S9	1256	(438/197).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
S10	1071	(438/287).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08

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S14	71	@ad<="20040326" and 'silicon oxide' near 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 17:21
S15	2	("6780720").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 10:15
S16	1	"6566205".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:16
S17	1	"6444592".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:16
S18	1	"6380104".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:18
S19	1	"6380056".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:19
S20	1	"6291867".PN.	USPÁT; USOCR	OR	ON	2005/08/03 10:21
S21	1	"6255204".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:21
S22	1	"6251761".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:22
S23	1	"6251729".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:23
S24	1	"6228721".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:24
S25	1	"6110784".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:24
S26	1	"6087208".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:25
S27	2	("6667251").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 10:33
S28	1	"5685949".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:29
S29	1	"6281138".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:29
S30	1	"20020197884".PN.	US-PGPUB	OR	ON	2005/08/03 10:29
S31	2	("5656516").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 10:33

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S32	1	"6444592".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:48
S33	1	"6372581".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:49
S34	0	@ad<="20040326" and 'silicon oxide' same 'nitrogen' with (replacing' or displacing') with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:52
S35	85	@ad<="20040326" and 'silicon oxide' same 'nitrogen' with (replac\$3' or displac\$3') with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:52
S36	2	("6136654").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 16:02
S37	2	"20040251495"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 16:02
S38	795	(438/787).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S39	574	(438/788).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S40	349	(438/789).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S41	280	(438/792).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:14
S42	1371	(438/197).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08

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S43	1128	(438/287).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 18:54
S44	1371	(438/197).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:11
S45	345	(438/216).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:11
S46	454	(438/791).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:14
S47	341	(438/775).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:15
S48	1	@ad<="20040326" and ultra adj1 thin with ("silicon oxide" or "silicon dioxide") near nitridat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 17:26
S49	1	"5693975".PN.	USPAT; USOCR	OR	ON	2006/04/26 17:25
S50	1	"5674788".PN.	USPAT; USOCR	OR	ON	2006/04/26 17:25
S52	53	@ad<="20040326" and ultra adj1 thin with ("silicon oxide" or "silicon dioxide" or "oxide") same nitridat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/26 19:03
S53	1	"20020146914".PN.	US-PGPUB	OR	ON	2006/04/26 17:32
S54	1	"20010027004".PN.	US-PGPUB	OR	ON	2006/04/26 17:34
S55	1	"6391724".PN.	USPAT; USOCR	OR	ON	2006/04/26 17:34
S56	1	"6235590".PN.	USPAT; USOCR	OR	ON	2006/04/26 17:35
S57	1	"6406960".PN.	USPAT; USOCR	OR	ON	2006/04/26 18:46
S58	1	"6323519".PN.	USPAT; USOCR	OR	ON	2006/04/26 18:47

						
S59	5	(("6,413,881") or ("6,548,366")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/26 18:55
S60	2	("6444592").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/26 19:01
S61	45	@ad<="20040326" and "ultra-thin" with ("silicon oxide" or "silicon dioxide" or "oxide") same nitridat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 08:55
S62	142	@ad<="20040326" and "ultra-thin" with ("silicon oxide" or "silicon dioxide" or "oxide") and nitridat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 09:01
S63	2	("6632747").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/27 08:57
S64	2	("6548366").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/27 08:57
S65	1	"6380056".PN.	USPAT; USOCR	OR	ON	2006/04/27 08:58
S66	1	"6326258".PN.	USPAT; USOCR	OR	ON	2006/04/27 08:58
S67	1	"6323143".PN.	USPAT; USOCR	OR	ON	2006/04/27 08:59
S68	1	"6136654".PN.	USPAT; USOCR	OR	ON	2006/04/27 08:59
S69	1	"6033998".PN.	USPAT; USOCR	OR	ON	2006/04/27 09:00
S70	45	@ad<="20040326" and nitridat\$4 same "ultra-thin" with ("silicon oxide" or "silicon dioxide" or "oxide")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 10:49
S71	122	@ad<="20040326" and nitridat\$4 same ("silicon oxide" or "silicon dioxide" or "oxide") with ("high k" or "high dielectric")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 10:54

S72	32	@ad<="20040326" and nitridat\$4 with ("silicon oxide" or "silicon dioxide" or "oxide") with ("high k" or "high dielectric")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 12:53
S73	1	"20030157771".PN.	US-PGPUB	OR	ON	2006/04/27 10:56
S74	1	"20020124867".PN.	US-PGPUB	OR	ON	2006/04/27 10:57
S76	390	@ad<="20040326" and nitridat\$3 and ("silicon oxide" or "silicon dioxide" or "oxide") same ("high k" or "high dielectric") same (nitride or "silicon nitride")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 11:49
\$77	84	@ad<="20040326" and nitridat\$3 same ("silicon oxide" or "silicon dioxide" or "oxide") same ("high k" or "high dielectric") same (nitride or "silicon nitride")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 12:53
S78	213	@ad<="20040326" and nitridat\$3 and ("silicon oxide" or "silicon dioxide" or "oxide") same ("high k" or "high dielectric") with (nitride or "silicon nitride")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 12:54
S79	14	@ad<="20040326" and nitridat\$3 with ("high k" or "high dielectric") with (nitride or "silicon nitride")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 12:57
S80	28	@ad<="20040326" and nitridat\$3 same ("high k" or "high dielectric") with "silicon nitride"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 13:05
S82	248	@ad<="20040326" and "gate dielectric" same ("high k" or "high dielectric") with "silicon nitride"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 13:06